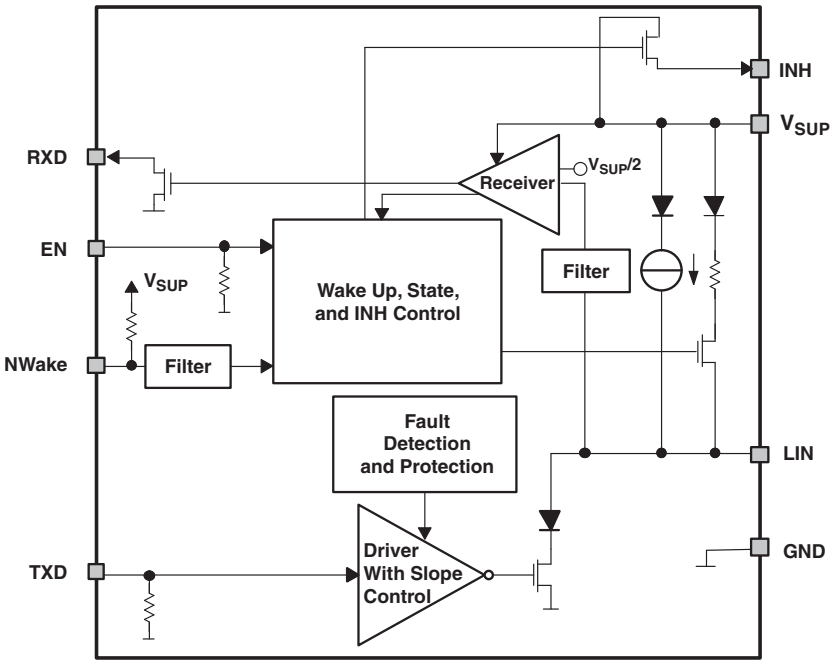
LIN AND MOST ECL PHYSICAL INTERFACE

Check for Samples: SN65HVDA195-Q1

FEATURES

- LIN Physical Layer Specification Revision 2.0 Compliant and Conforms to SAEJ2602 Recommended Practice for LIN
- LIN Bus Speed up to 20-kbps LIN Specified Maximum and MOST ECL Speeds Down to 0 Baud
- Supports ISO9141 (K-Line)
- Qualified for Automotive Applications
- Sleep Mode: Ultra Low Current Consumption, Allows Wake-Up Events From LIN Bus, Wake-Up Input (External Switch), or Host Microcontroller
- High-Speed Receive Capable
- ESD Protection to ±12 kV (Human-Body Model) on LIN Pin
- LIN Pin Handles Voltage From –40 V to 40 V
- Survives Transient Damage in Automotive Environment (ISO 7637)
- Extended Operation With Supply From 7 V to 27 V DC (LIN Specification 7 V to 18 V)
- Interfaces to Microcontroller With 5-V or 3.3-V I/O Pins
- Wake-Up Request on RXD Pin
- Control of External Voltage Regulator (INH Pin)
- Integrated Pullup Resistor and Series Diode for LIN Slave Applications
- Low Electromagnetic Emission (EME), High Electromagnetic Immunity (EMI)
- Bus Terminal Short Circuit Protected for Short to Battery or Short to Ground
- Thermally Protected
- Ground Disconnection Fail Safe at System Level
- Ground Shift Operation at System Level
- Unpowered Node Does Not Disturb the Network

FUNCTIONAL BLOCK DIAGRAM



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DESCRIPTION

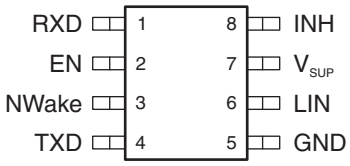
The SN65HVDA195 is the Local Interconnect Network (LIN) physical interface and MOST ECL interface, which integrates the serial transceiver with wake-up and protection features. The bus is a single-wire bidirectional bus typically used for low-speed in-vehicle networks using data rates to 20 kbps. The device can transmit with an effective data rate of 0 kbps since it does not have dominant state time out. The protocol output data stream on TXD is converted by the SN65HVDA195 into the bus signal through a current-limited wave-shaping driver as outlined by the LIN Physical Layer Specification Revision 2.0. The receiver converts the data stream from the bus and outputs the data stream via RXD. The bus has two states: dominant state (voltage near ground) and the recessive state (voltage near battery). In the recessive state, the bus is pulled high by the SN65HVDA195's internal pullup resistor and series diode, so no external pullup components are required for slave applications. Master applications require an external pullup resistor (1 kΩ) plus a series diode per the LIN specification.

In sleep mode, the SN65HVDA195 requires low quiescent current even though the wake-up circuits remain active, allowing for remote wake up via the LIN bus or local wake up via the NWake or EN pins.

The SN65HVDA195 has been designed for operation in the harsh automotive environment. The device can handle LIN bus voltage swings from 40 V down to ground and survive –40 V. The device also prevents back-feed current through LIN to the supply input, in case of a ground shift or supply voltage disconnection. It also features undervoltage, overtemperature, and loss-of-ground protection. In the event of a fault condition, the output is immediately switched off and remains off until the fault condition is removed.

TERMINAL FUNCTIONS

D PACKAGE
(TOP VIEW)



TERMINAL ASSIGNMENTS

PIN		TYPE	DESCRIPTION
NAME	NO.		
RXD	1	O	RXD output (open drain) interface reporting state of LIN bus voltage
EN	2	I	Enable input
NWake	3	I	High voltage input for device wake up
TXD	4	I	TXD input interface to control state of LIN output
GND	5	GND	Ground
LIN	6	I/O	LIN bus single-wire transmitter and receiver
V_{SUP}	7	Supply	Device supply voltage (connected to battery in series with external reverse blocking diode)
INH	8	O	Inhibit controls external voltage regulator with inhibit input

ORDERING INFORMATION(1)

T_A	PACKAGE (2)		ORDERABLE PART NUMBER	TOP-SIDE MARKING
–40°C to 125°C	SOIC – D	Reel of 2500	SN65HVDA195QDRQ1	A195Q

(1) For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI web site at www.ti.com.
(2) Package drawings, thermal data, and symbolization are available at www.ti.com/packaging.

Local Interconnect Network (LIN) Bus

This I/O pin is the single-wire LIN bus transmitter and receiver.

Transmitter Characteristics

The driver is a low-side transistor with internal current limitation and thermal shutdown. There is an internal 30-kΩ pullup resistor with a serial diode structure to V_{SUP}, so no external pullup components are required for LIN slave mode applications. An external pullup resistor of 1 kΩ, plus a series diode to V_{SUP} must be added when the device is used for master node applications.

Voltage on LIN can go from –40-V to 40-V dc without any currents other than through the pullup resistance. There are no reverse currents from the LIN bus to supply (V_{SUP}), even in the event of a ground shift or loss of supply (V_{SUP}).

The LIN thresholds and ac parameters are LIN Protocol Specification Revision 2.0 compliant.

During a thermal shut down condition, the driver is disabled.

Receiver Characteristics

The receiver's characteristic thresholds are ratio-metric with the device supply pin. Typical thresholds are 50%, with a hysteresis between 5% and 17.5% of supply.

The receiver is capable of receiving higher data rates (>100 kbps) than supported by LIN or SAEJ2602 specifications. This allows the SN65HVDA195 to be used for high-speed downloads at end-of-line production or other applications. The actual data rates achievable depend on system time constants (bus capacitance and pullup resistance) and driver characteristics used in the system.

Transmit Input (TXD)

TXD is the interface to the MCU's LIN protocol controller or SCI/UART used to control the state of the LIN output. When TXD is low, the LIN output is dominant (near ground). When TXD is high, the LIN output is recessive (near battery). The TXD input structure is compatible with microcontrollers with 3.3-V and 5-V I/O. TXD has an internal pulldown resistor. This device does not have a TXD dominant time out protection circuit so that low data rates may be used.

Receive Output (RXD)

RXD is the interface to the MCU's LIN protocol controller or SCI/UART, which reports the state of the LIN bus voltage. LIN recessive (near battery) is represented by a high level on RXD and LIN dominant (near ground) is represented by a low level on RXD. The RXD output structure is an open-drain output stage. This allows the SN65HVDA195 to be used with 3.3-V and 5-V I/O microcontrollers. If the microcontroller's RXD pin does not have an integrated pullup, an external pullup resistor to the microcontroller I/O supply voltage is required.

RXD Wake-up Request

When the SN65HVDA195 has been in low-power mode and encounters a wake-up event from the LIN bus or NWake pin, RXD goes low, while the device enters and remains in standby mode (until EN is reasserted high and the device enters normal mode).

Supply Voltage (V_{SUP})

V_{SUP} is the SN65HVDA195 device power supply pin. V_{SUP} is connected to the battery through an external reverse battery blocking diode. The characterized operating voltage range for the SN65HVDA195 is from 7 V to 27 V. V_{SUP} is protected for harsh automotive conditions up to 40 V.

The device contains a reset circuit to avoid false bus messages during undervoltage conditions when V_{SUP} is less than V_{SUP_UNDER}.

Ground (GND)

GND is the SN65HVDA195 device ground connection. The SN65HVDA195 can operate with a ground shift as long as the ground shift does not reduce V_{SUP} below the minimum operating voltage. If there is a loss of ground at the ECU level, the SN65HVDA195 does not have a significant current consumption on LIN bus.

Enable Input (EN)

EN controls the operation mode of the SN65HVDA195 (normal or sleep mode). When EN is high, the SN65HVDA195 is in normal mode allowing a transmission path from TXD to LIN and from LIN to RXD. When EN is low the device is put into sleep mode and there are no transmission paths available. The device can enter normal mode only after being woken up. EN has an internal pulldown resistor to ensure the device remains in low-power mode even if EN floats.

NWake Input (NWake)

NWake is a high-voltage input used to wake up the SN65HVDA195 from low-power mode. NWake is usually connected to an external switch in the application. A low on NWake that is asserted longer than the filter time (t_{NWAKE}) results in a local wake-up. NWake provides an internal pullup source to V_{SUP}.

Inhibit Output (INH)

INH is used to control an external voltage regulator that has an inhibit input. When the SN65HVDA195 is in normal operating mode, the inhibit high-side switch is enabled and the external voltage regulator is activated. When SN65HVDA195 is in low-power mode, the inhibit switch is turned off, which disables the voltage regulator. A wake-up event on for the SN65HVDA195 returns INH to V_{SUP} level. INH can also drive an external transistor connected to an MCU interrupt input.

OPERATING STATES

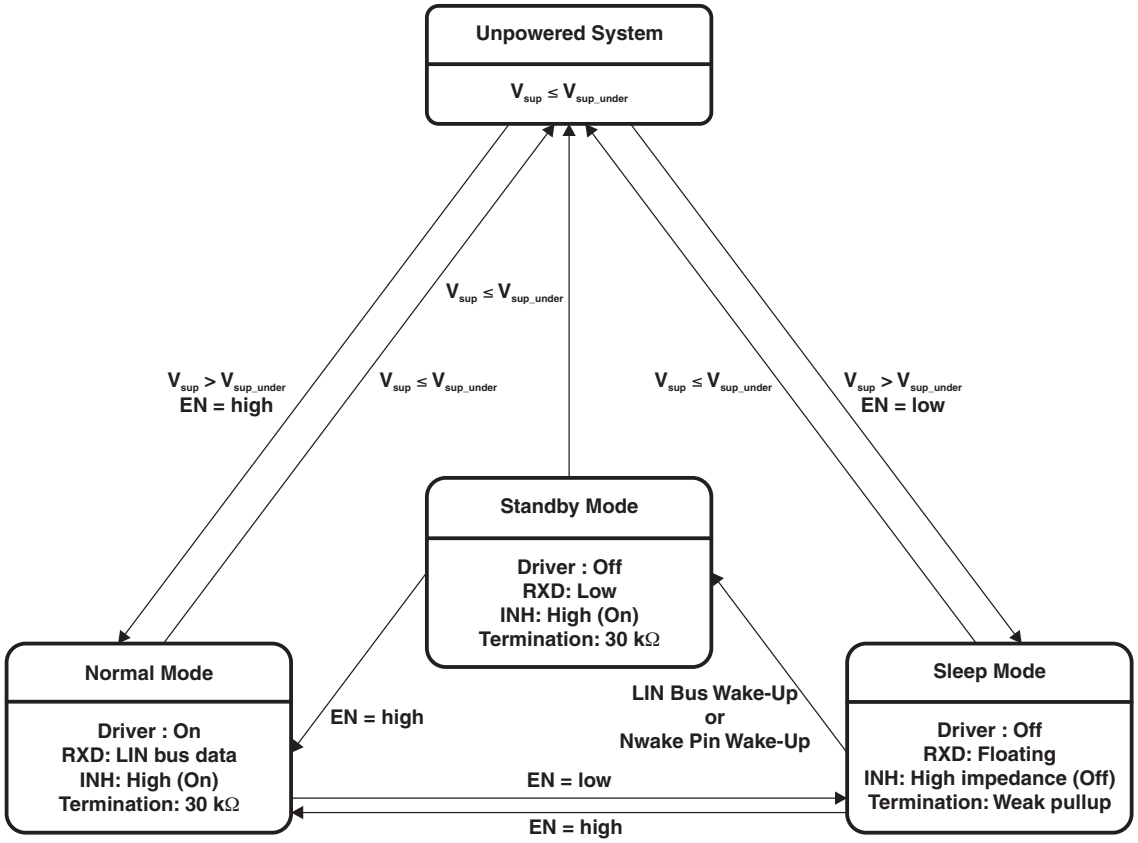


Figure 1. Operating States Diagram

Table 1. Operating Modes

MODE	EN	RXD	LIN BUS TERMINATION	INH	TRANSMITTER	COMMENTS
Sleep	Low	Floating	Weak current pullup	High impedance	Off	
Standby	Low	Low	30 kΩ (typ)	High	Off	Wake-up event detected, waiting on MCU to set EN
Normal	High	LIN bus data	30 kΩ (typ)	High	On	LIN transmission up to 20 kbps

Normal Mode

This is the normal operational mode, in which the receiver and driver are active, and LIN transmission up to the LIN specified maximum of 20 kbps is supported. The receiver detects the data stream on the LIN bus and outputs it on RXD for the LIN controller, where recessive on the LIN bus is a digital high, and dominate on the LIN bus is digital low. The driver transmits input data on TXD to the LIN bus. Normal mode is entered as EN transitions high while the SN65HVDA195 is in sleep or standby mode.

Sleep Mode

Sleep mode is the power saving mode for the SN65HVDA195 and the default state after power up (assuming EN is low during power up). Even with the extremely low current consumption in this mode, the SN65HVDA195 can still wake up from LIN bus via a wake-up signal, a low on NWake, or if EN is set high. The LIN bus and NWake are filtered to prevent false wake-up events. The wake-up events must be active for their respective time periods (t_{LINBUS}, t_{NWake}).

The sleep mode is entered by setting EN low.

While the device is in sleep mode, the following conditions exist:

- The LIN bus driver is disabled and the internal LIN bus termination is switched off (to minimize power loss if LIN is short circuited to ground). However, the weak current pullup is active to prevent false wake-up events in case an external connection to the LIN bus is lost.
- The normal receiver is disabled.
- INH is high impedance.
- EN input, NWake input, and the LIN wake-up receiver are active.

Wake-Up Events

There are three ways to wake up the SN65HVDA195 from sleep mode:

- Remote wake-up via recessive (high) to dominant (low) state transition on LIN bus. The dominant state must be held for t_{LINBUS} filter time and then the bus must return to the recessive state (to eliminate false wake-ups from disturbances on the LIN bus or if the bus is shorted to ground).
- Local wake-up via a low on NWake, which is asserted low longer than the filter time t_{NWake} (to eliminate false wake-ups from disturbances on NWake)
- Local wake-up via EN being set high

Standby Mode

This mode is entered whenever a wake-up event occurs via LIN bus or NWake while the SN65HVDA195 is in sleep mode. The LIN bus slave termination circuit and INH are turned on when standby mode is entered. The application system powers up once INH is turned on, assuming the system is using a voltage regulator connected via INH. Standby mode is signaled via a low level on RXD.

When EN is set high while the SN65HVDA195 is in standby mode the device returns to normal mode and the normal transmission paths from TXD to LIN bus and LIN bus to RXD are enabled.

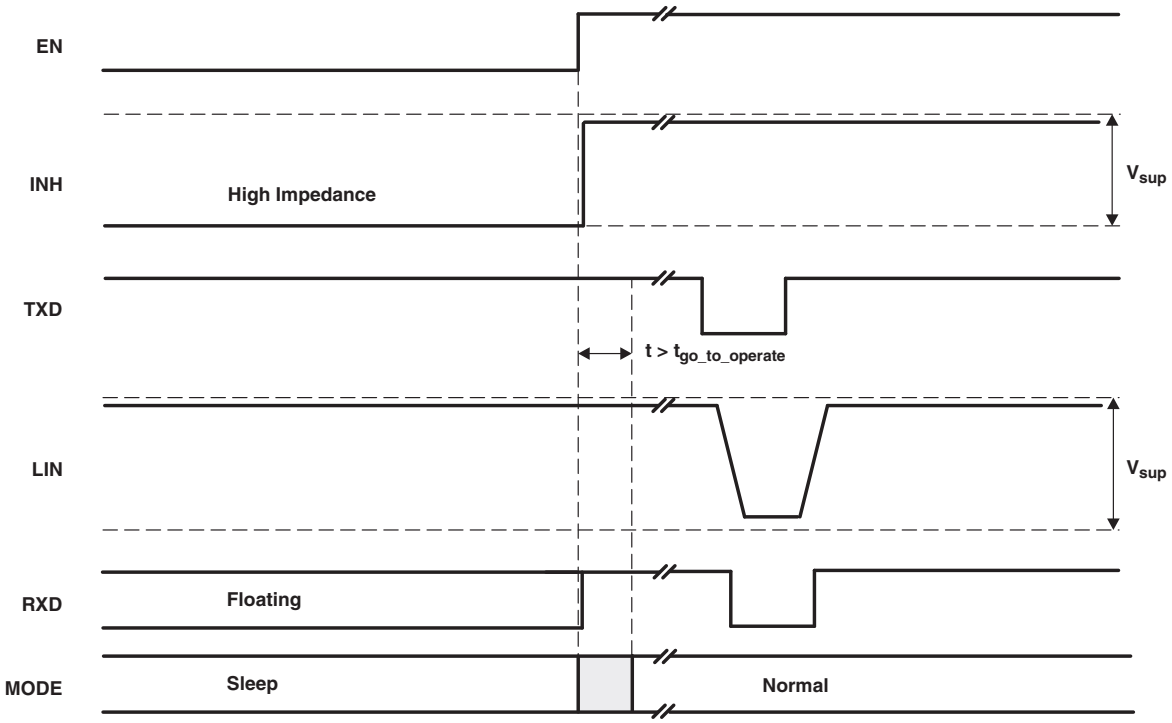


Figure 2. Wake-Up Via EN

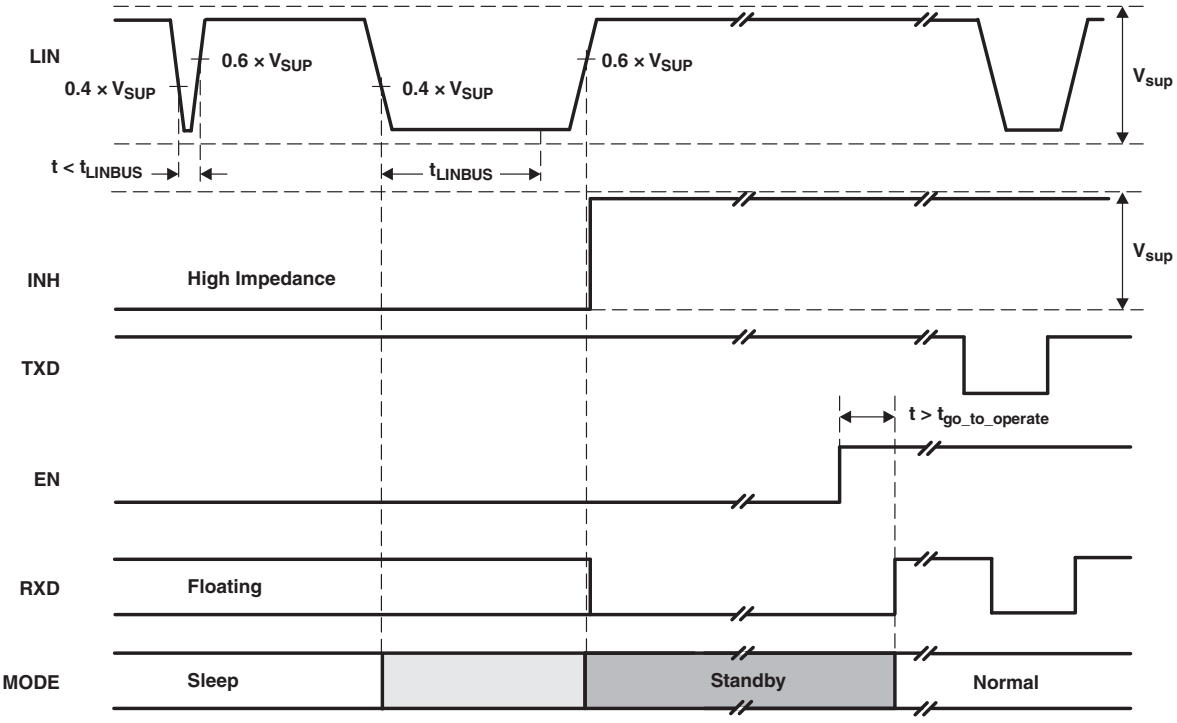


Figure 3. Wake-Up Via LIN

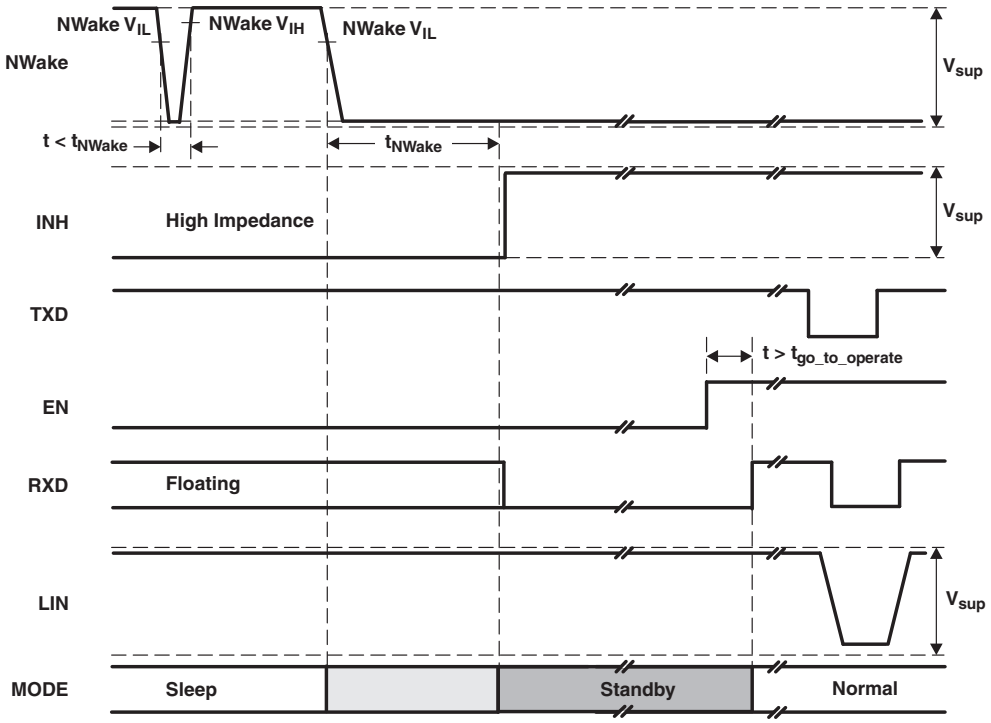


Figure 4. Wake-Up Via NWake

ABSOLUTE MAXIMUM RATINGS(1)

over operating free-air temperature range (unless otherwise noted)

	PARAMETER				RATING	UNIT
1.1	V_{SUP} (2)	Supply line supply voltage(3)			0 to 40	V
1.2	V_{NWake}	NWake dc and transient input voltage (through serial resistor)			–0.3 to 40	
1.3	I_{NWake}	N_{Wake} current if due to ground shifts $V_{NWake} \le V_{GND}$ – 0.3 V, thus the current into NWake must be limited via a serial resistance.			–3.6	mA
1.4	V_{INH}	INH voltage			–0.3 to V_{SUP} + 0.3	V
1.5	V_{Logic_Input}	Logic pin input voltage	RXD, TXD, EN		–0.3 to 5.5	
1.6	V_{LIN}	LIN dc-input voltage			–40 to 40	
1.7	ESD	Electrostatic discharge	Human-Body Model	LIN(4)	–12 to 12	kV
1.8				NWake(4)	–11 to 11	
1.9				All other pins(4)	–4 to 4	
1.10			Charged-Device Model	All pins(5)	–1500 to 1500	V
1.11	T_A	Operational free-air temperature range			–40 to 125	°C
1.12	T_J	Junction temperature range			–40 to 150	
1.13	$T_{Storage}$	Storage temperature range			–40 to 165	
1.14	$R_{\theta JA}$	Thermal resistance, junction to ambient			145	°C/W
1.15	T_{SD}	Thermal shutdown			200	°C
1.16	T_{SD_HYS}	Thermal shutdown hysteresis			25	

(1) Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) All voltage values are with respect to GND.
(3) The device is specified for operation in the range of V_{SUP} from 7 V to 27 V. Operating the device above 27 V may significantly raise the junction temperature of the device and system level thermal design needs to be considered.
(4) The human body model is a 100-pF capacitor discharged through a 1.5-kΩ resistor into each pin.
(5) Tested in accordance to JEDEC Standard 22, Test Method C101 (JESD22-C101).

ELECTRICAL CHARACTERISTICS

V_{SUP} = 7 V to 27 V, T_A = –40°C to 125°C (unless otherwise noted)

PARAMETER			TEST CONDITIONS	MIN	TYP (1)	MAX	UNIT
SUPPLY							
2.1		Operational supply voltage (2)	Device is operational beyond the LIN 2.0 defined nominal supply line voltage range of 7 V ≤ V_{SUP} ≤ 18 V	7	14	27	V
2.2		Nominal supply line voltage	Normal and standby modes	7	14	18	
2.3			Sleep mode	7	12	18	
2.4		V_{SUP} undervoltage threshold			4.8	6.0	
2.5	I_{SUP}	Supply current	Normal mode, EN = High, Bus dominant (total bus load where R_{LIN} ≥ 500 Ω and C_{LIN} ≤ 10 nF (see Figure 7) (3), INH = V_{SUP}, NWake = V_{SUP}		1.2	7.5	mA
2.6			Standby mode, EN = low, Bus dominant (total bus load where R_{LIN} ≥ 500 Ω and C_{LIN} ≤ 10 nF (see Figure 7) (3), INH = V_{SUP}, NWake = V_{SUP}		1	2.1	
2.7			Normal mode, EN = High, Bus recessive, LIN = V_{SUP}, INH = V_{SUP}, NWake = V_{SUP}		450	775	µA
2.8			Standby mode, EN = Low, Bus recessive, LIN = V_{SUP}, INH = V_{SUP}, NWake = V_{SUP}		450	775	
2.9			Sleep mode, EN = 0, T_A = –40°C to 95°C, 7 V < V_{SUP} ≤ 12 V, LIN = V_{SUP}, NWake = V_{SUP}		13	26	
2.10			Sleep mode, EN = 0, T_A = –40°C to 95°C, 12 V < V_{SUP} < 18 V, LIN = V_{SUP}, NWake = V_{SUP}			35	
2.11	ΔI_{SUP}	Delta supply current in sleep mode	Sleep mode, EN = 0, T_A = –40°C to 95°C, Supply line voltage range of 7 V ≤ V_{SUP} ≤ 18 V, LIN bus voltage: V_{SUP} – 1.85 V ≤ LIN ≤ V_{SUP}			20	
RXD OUTPUT PIN							
3.1	V_O	Output voltage		–0.3		5.5	V
3.2	I_{OL}	Low-level output current, open drain	LIN = 0 V, RXD = 0.4 V	3.5			mA
3.3	I_{IKG}	Leakage current, high-level	LIN = V_{SUP}, RXD = 5 V	–5	0	5	µA
TXD INPUT PIN							
4.1	V_{IL}	Low-level input voltage		–0.3		0.8	V
4.2	V_{IH}	High-level input voltage		2		5.5	
4.3	V_{IT}	Input threshold hysteresis voltage		30		500	mV
4.4		Pulldown resistor		125	350	800	kΩ
4.5	I_{IL}	Low-level input current	TXD = Low	–5	0	5	µA

(1) Typical values are given for V_{SUP} = 14 V at 25°C, except for low power mode where typical values are given for V_{SUP} = 12 V at 25°C.
(2) All voltages are defined with respect to ground; positive currents flow into the SN65HVDA195 device.
(3) In the dominant state, the supply current increases as the supply voltage increases due to the integrated LIN slave termination resistance. At higher voltages the majority of supply current is through the termination resistance. The minimum resistance of the LIN slave termination is 20 kΩ, so the maximum supply current attributed to the termination is:

$I_{SUP\ (dom)\ max\ termination}$ $(V_{SUP} – (V_{LIN\_Dominant} + 0.7\ V) / 20\ k\Omega$

ELECTRICAL CHARACTERISTICS (continued)

V_{SUP} = 7 V to 27 V, T_A = –40°C to 125°C (unless otherwise noted)

PARAMETER			TEST CONDITIONS	MIN	TYP (1)	MAX	UNIT
LIN PIN (Referenced to V_{SUP})							
5.1	V_{OH}	High-level output voltage	LIN recessive, TXD = High, I_O = 0 mA, V_{SUP} = 14 V	V_{SUP} – 1			V
5.2	V_{OL}	Low-level output voltage	LIN dominant, TXD = Low, I_O = 40 mA, V_{SUP} = 14 V	0		0.2 × V_{SUP}	V
5.3	R_{slave}	Pullup resistor to V_{SUP}	Normal and standby modes	20	30	60	kΩ
5.4		Pullup current source to V_{SUP}	Sleep mode, V_{SUP} = 14 V, LIN = GND	–2		–20	µA
5.5	I_L	Limiting current	TXD = 0 V	45	160	220	mA
5.6			TXD = 0 V, T_A = –10°C to 125°C			200	
5.7	I_{LKG}	Leakage current	LIN = V_{SUP}	–5	0	5	µA
5.8	I_{LKG}	Leakage current, loss of supply	7 V < LIN ≤ 12 V, V_{SUP} = GND			5	µA
5.9			12 V < LIN < 18 V, V_{SUP} = GND			10	
5.10	V_{IL}	Low-level input voltage	LIN dominant			0.4 × V_{SUP}	V
5.11	V_{IH}	High-level input voltage	LIN recessive	0.6 × V_{SUP}			
5.12	V_{IT}	Input threshold voltage		0.4 × V_{SUP}	0.5 × V_{SUP}	0.6 × V_{SUP}	
5.13	V_{hys}	Hysteresis voltage		0.05 × V_{SUP}		0.175 × V_{SUP}	
5.14	V_{IL}	Low-level input voltage for wake-up				0.4 × V_{SUP}	
EN PIN							
6.1	V_{IL}	Low-level input voltage		–0.3		0.8	V
6.2	V_{IH}	High-level input voltage		2		5.5	V
6.3	V_{hys}	Hysteresis voltage		30		500	mV
6.4		Pulldown resistor		125	350	800	kΩ
6.5	I_{IL}	Low-level input current	EN = Low	–5	0	5	µA
INH PIN							
7.1	V_o	DC output voltage		–0.3		V_{SUP} + 0.3	V
7.2	R_{on}	On state resistance	Between V_{SUP} and INH, INH = 2-mA drive, Normal or standby mode		35	85	Ω
7.3	I_{IKG}	Leakage current	Low-power mode, 0 < INH < V_{SUP}	–5	0	5	µA
NWake PIN							
8.1	V_{IL}	Low-level input voltage		–0.3		V_{SUP} – 3.3	V
8.2	V_{IH}	High-level input voltage		V_{SUP} – 1		V_{SUP} + 0.3	V
8.3		Pullup current	NWake = 0 V	–45	–10	–2	µA
8.4	I_{IKG}	Leakage current	V_{SUP} = NWake	–5	0	5	µA
THERMAL SHUTDOWN							
9.1		Shutdown junction thermal temperature			190		°C

ELECTRICAL CHARACTERISTICS (continued)

V_{SUP} = 7 V to 27 V, T_A = –40°C to 125°C (unless otherwise noted)

PARAMETER			TEST CONDITIONS	MIN	TYP (1)	MAX	UNIT
AC CHARACTERISTICS							
10.1	D1	Duty cycle 1(4)	$TH_{REC(max)}$ = 0.744 × V_{SUP}, $TH_{DOM(max)}$ = 0.581 × V_{SUP}, V_{SUP} = 7 V to 18 V, t_{BIT} = 50 µs (20 kbps), D1 = $t_{Bus\_rec(min)}$/ (2 × t_{BIT}). See Figure 5	0.396			
10.2	D2	Duty cycle 2(4)	$TH_{REC(min)}$ = 0.422 × V_{SUP}, $TH_{DOM(min)}$ = 0.284 × V_{SUP}, V_{SUP} = 7.6 V to 18 V, t_{BIT} = 50 µs (20 kbps), D2 = $t_{Bus\_rec(max)}$/ (2 × t_{BIT}). See Figure 5			0.581	
10.3	D3	Duty cycle 3(4)	$TH_{REC(max)}$ = 0.778 × V_{SUP}, $TH_{DOM(max)}$ = 0.616 × V_{SUP}, V_{SUP} = 7 V to 18 V, t_{BIT} = 96 µs (10.4 kbps), D3 = $t_{Bus\_rec(min)}$/ (2 × t_{BIT}). See Figure 5	0.417			
10.4	D4	Duty cycle 4(4)	$TH_{REC(min)}$ = 0.389 × V_{SUP}, $TH_{DOM(min)}$ = 0.251 × V_{SUP}, V_{SUP} = 7.6 V to 18 V, t_{BIT} = 96 µs (10.4 kbps), D4 = $t_{Bus\_rec(max)}$/ (2 × t_{BIT}). See Figure 5			0.59	
10.5	t_{rx_pdr}	Receiver rising propagation delay time	R_{RXD} = 2.4 kΩ, C_{RXD} = 20 pF See Figure 6 See Figure 7			6	µs
10.6	t_{rx_pdf}	Receiver falling propagation delay time	R_{RXD} = 2.4 kΩ, C_{RXD} = 20 pF See Figure 6 See Figure 7			6	
10.7	t_{rx_sym}	Symmetry of receiver propagation delay time	rising edge with respect to falling edge (t_{rx_sym} = t_{rx_pdf} – t_{rx_pdr}) R_{RXD} = 2.4 kΩ, C_{RXD} = 20 pF See Figure 6 See Figure 7	–2		2	
10.8	t_{NWake}	NWake filter time for local wake-up	See Figure 4	25	50	150	
10.9	t_{LINBUS}	LIN wake-up filter time (dominant time for wake-up via LIN bus)	See Figure 3	25	50	150	
10.10	$t_{go\_to\_operate}$		See Figure 2 to Figure 3		0.5	1	

(4) Duty cycles: LIN driver bus load conditions (C_{LINBUS}, R_{LINBUS}): Load1 = 1 nF, 1 kΩ; Load2 = 10 nF, 500 Ω. Duty cycles 3 and 4 are defined for 10.4-kbps operation. The SN65HVDA195 also meets these lower data rate requirements, while it is capable of the higher speed 20-kbps operation as specified by Duty cycles 1 and 2. SAEJ2602 derives propagation delay equations from the LIN 2.0 duty cycle definitions, for details see the SAEJ2602 specification.

TIMING DIAGRAMS

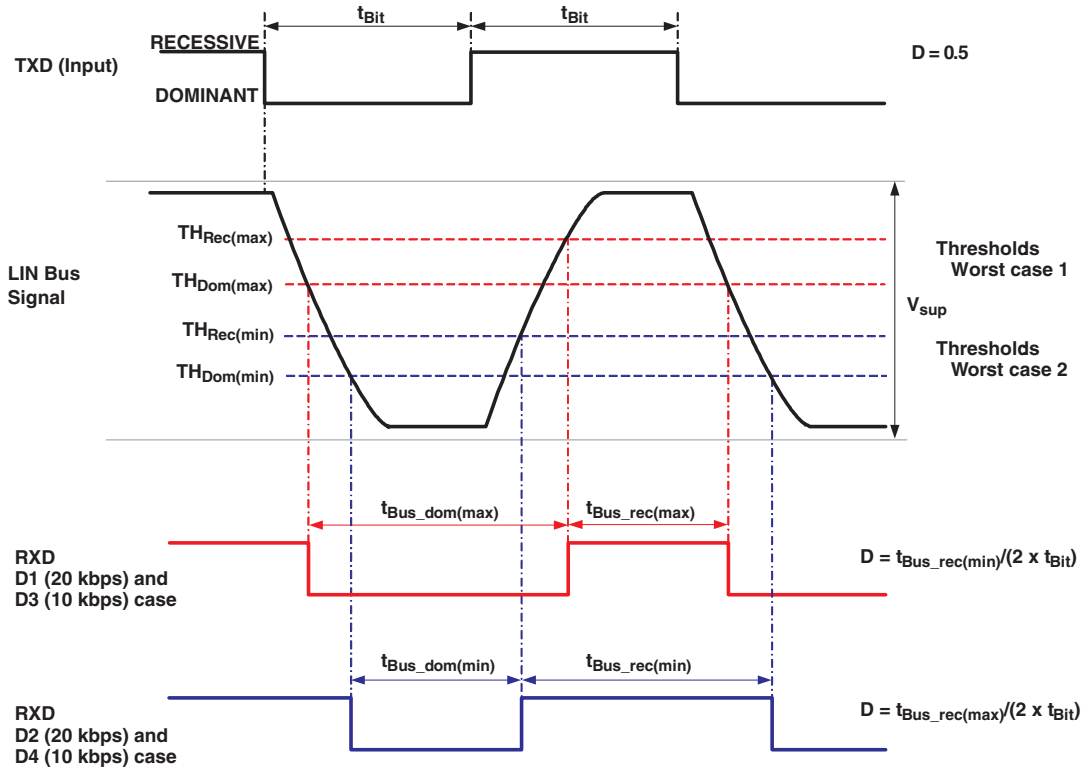


Figure 5. Definition of Bus Timing Parameters

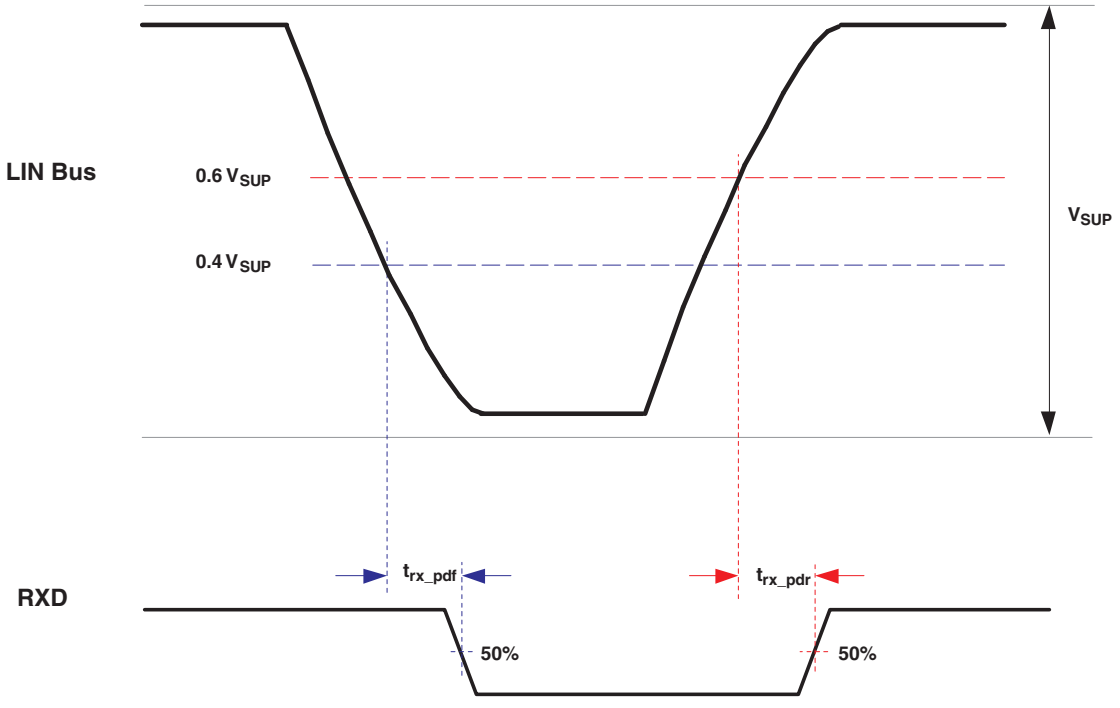


Figure 6. Propagation Delay

TIMING DIAGRAMS (continued)

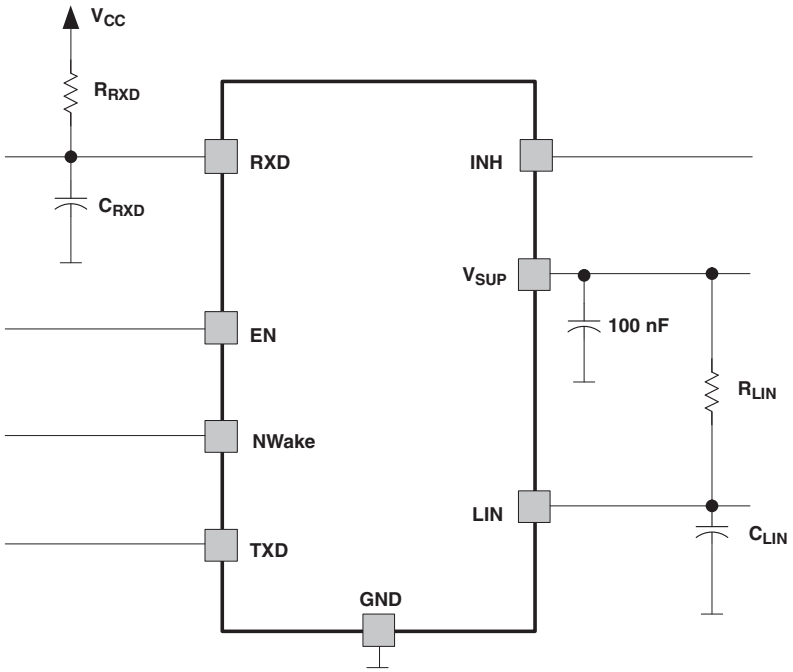
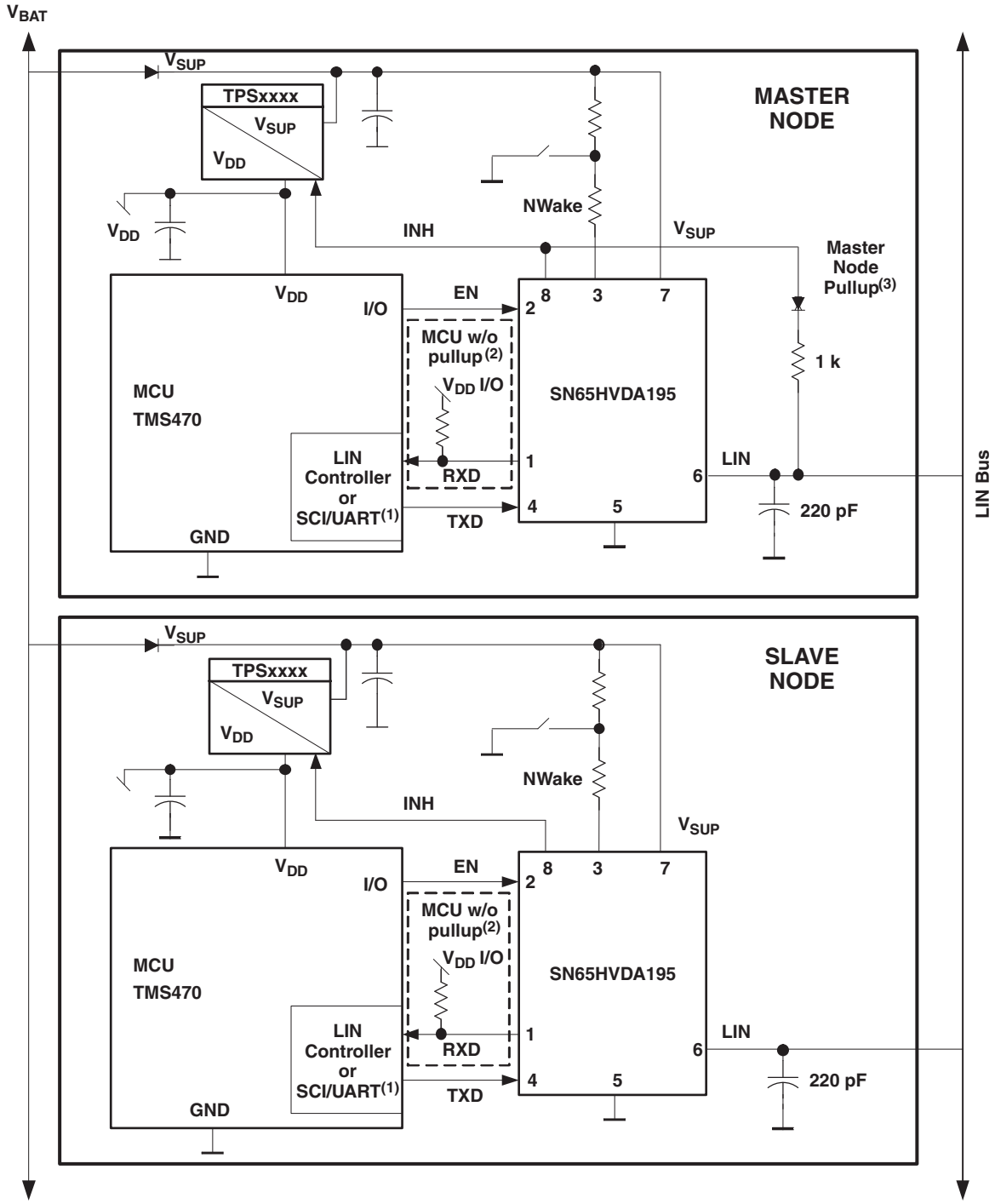


Figure 7. Test Circuit for AC Characteristics

APPLICATION INFORMATION



(1) RXD on MCU or LIN slave has internal pullup, no external pullup resistor is needed.

(2) RXD on MCU or LIN slave without internal pullup, requires external pullup resistor.

(3) Master node applications require an external 1-kΩ pullup resistor and serial diode.

Figure 8.

Device Comparison: TPIC1021A vs SN65HVDA195

The SN65HVDA195 is pin-to-pin compatible to the TPIC1021 and TPIC1021A devices. The SN65HVDA195 is functionally equivalent to the TPIC1021A but with the TXD dominant state timeout protection removed. Table 2 is a summary of the differences between the two devices.

Table 2. SN65HVDA195 vs TPIC1021A Differences

SPECIFICATION	TPIC1021A	SN65HVDA195
TXD Dominant State Timeout	TXD held dominant for longer than t_{DST} will disable the LIN driver to protect the LIN bus from being dominant during a hardware or software fault shorting TXD dominant	No dominant state time-out on TXD allowing extremely low data rate and additional applications using the device.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish	MSL Peak Temp (3)	Op Temp (°C)	Top-Side Markings (4)	Samples
SN65HVDA195QDRQ1	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	A195Q	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

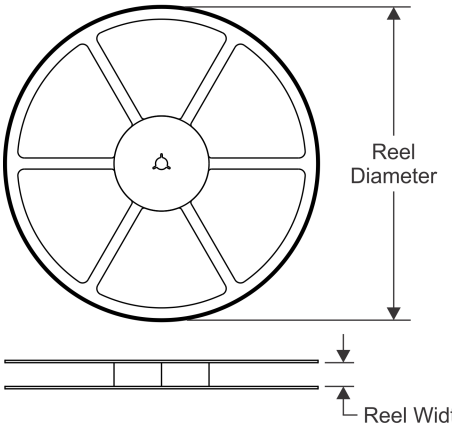
(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.
TBD: The Pb-Free/Green conversion plan has not been defined.
Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.
Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.
Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

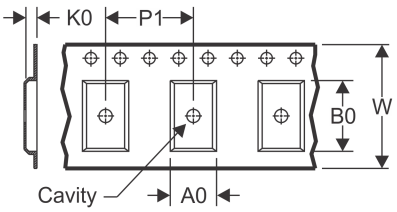
(4) Only one of markings shown within the brackets will appear on the physical device.

TAPE AND REEL INFORMATION

REEL DIMENSIONS

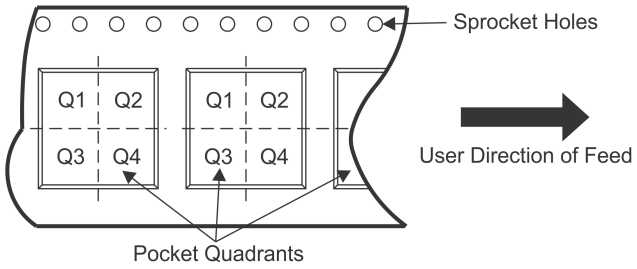


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

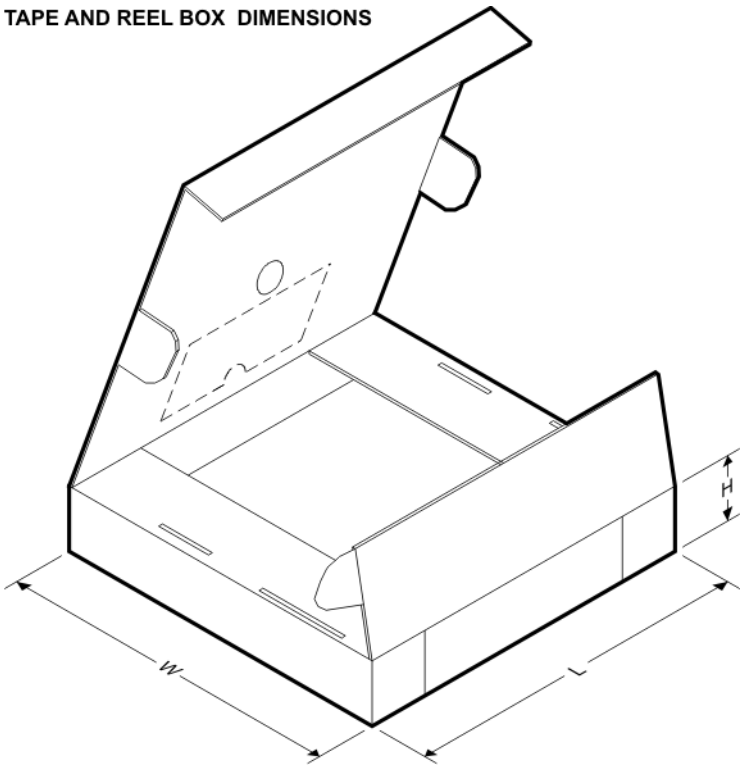
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN65HVDA195QDRQ1	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1

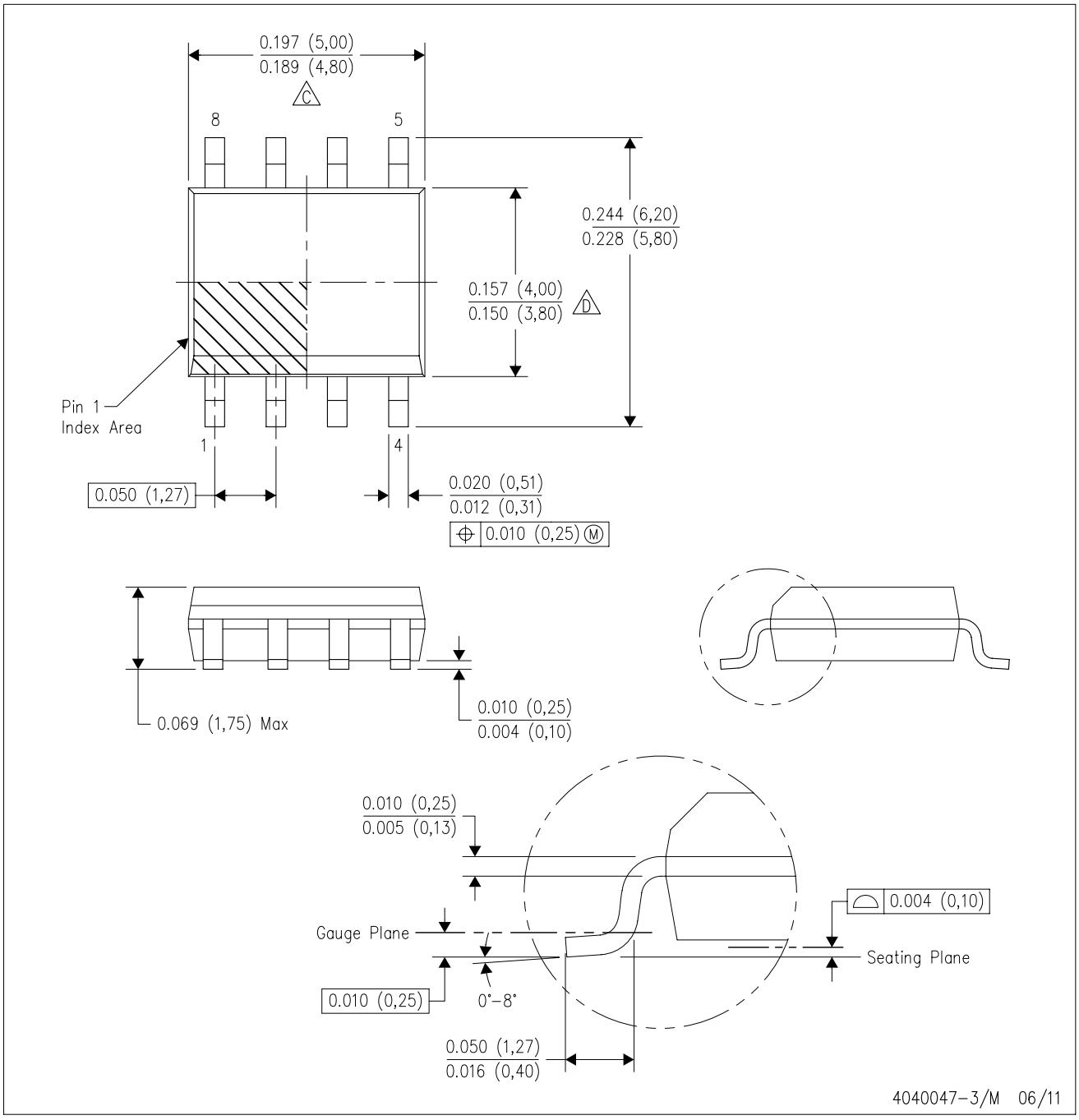
TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

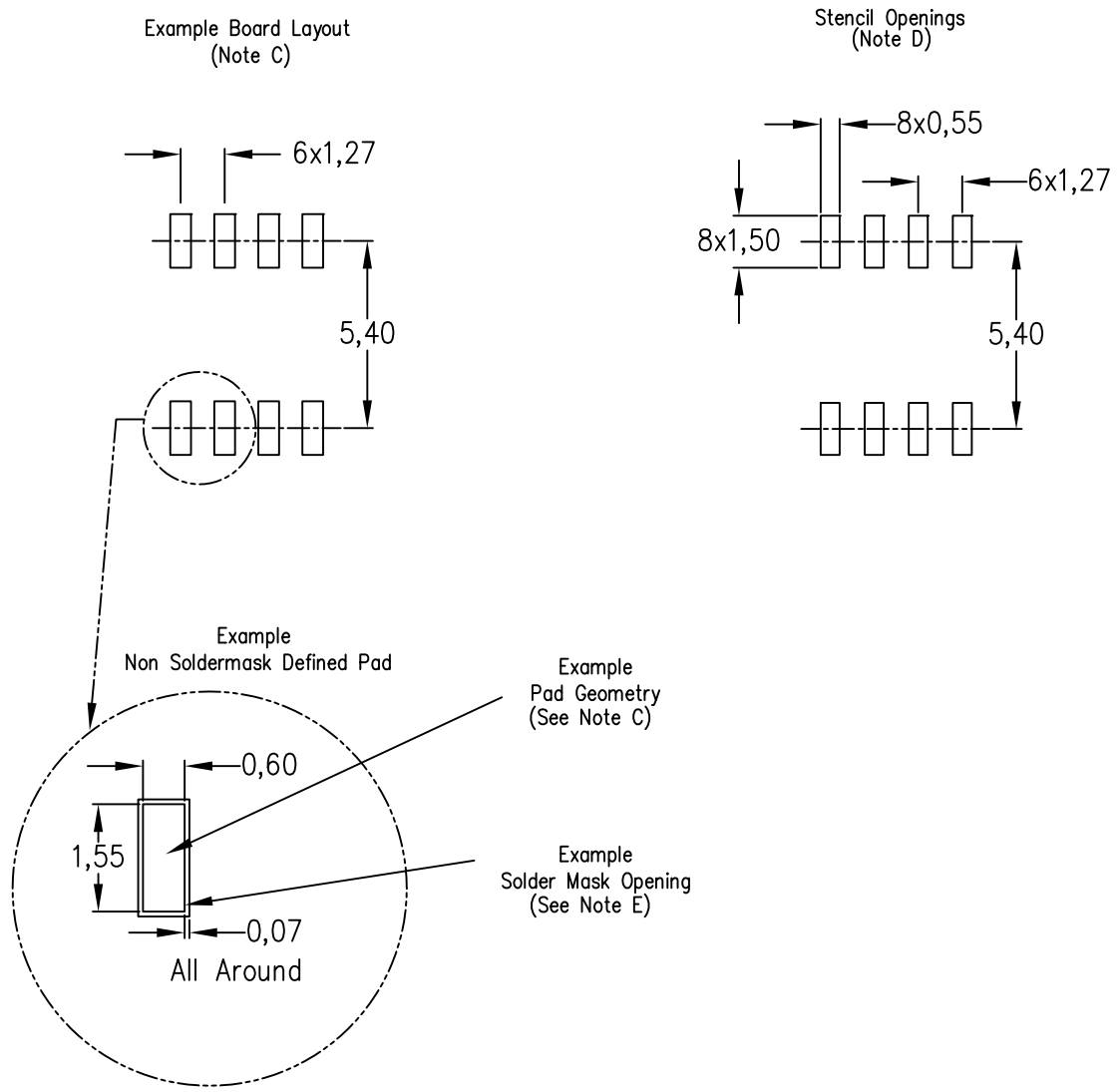
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN65HVDA195QDRQ1	SOIC	D	8	2500	367.0	367.0	35.0

D (R–PDSO–G8) PLASTIC SMALL OUTLINE



NOTES:
A. All linear dimensions are in inches (millimeters).
B. This drawing is subject to change without notice.
C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
D. Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
E. Reference JEDEC MS–012 variation AA.

D (R–PDSO–G8) PLASTIC SMALL OUTLINE



NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Publication IPC–7351 is recommended for alternate designs.
D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC–7525 for other stencil recommendations.
E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

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